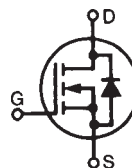


PolarHV™ HiPerFET IXFP7N80PM

Power MOSFET

(Electrically Isolated Tab)

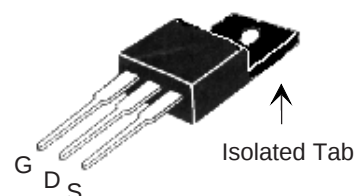
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



$$\begin{aligned} V_{DSS} &= 800 \text{ V} \\ I_{D25} &= 3.5 \text{ A} \\ R_{DS(on)} &\leq 1.44 \text{ } \Omega \\ t_{rr} &\leq 250 \text{ ns} \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	800	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	800	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	3.5	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	18	A
I_{AR}	$T_C = 25^\circ\text{C}$	4	A
E_{AR}	$T_C = 25^\circ\text{C}$	20	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	300	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 10 \text{ } \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	50	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 s	260	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		3.0	g

OVERMOLDED TO-220
(IXTP...M) OUTLINE



G = Gate D = Drain
S = Source

Features

- Plastic overmolded tab for electrical isolation
- Fast intrinsic diode
- International standard package
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

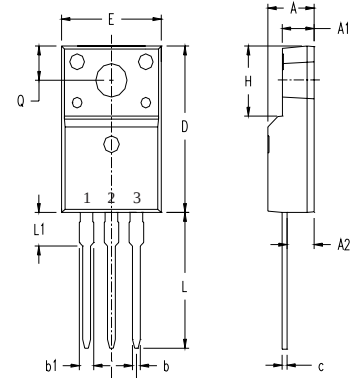
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \text{ } \mu\text{A}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$			25 μA
	$V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			500 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 3.5 \text{ A}$ Note 1			1.44 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{ V}$; $I_D = 3.5\text{ A}$, Note 1	5	9.5	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		1890	pF
C_{oss}			133	pF
C_{rss}			13	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 4\text{ A}$ $R_G = 10\ \Omega$ (External)		28	ns
t_r			32	ns
$t_{d(off)}$			55	ns
t_f			24	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 6\text{ A}$		32	nC
Q_{gs}			12	nC
Q_{gd}			9	nC
R_{thJC}				2.5 $^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			7 A
I_{SM}	Repetitive			18 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, Note 1			1.5 V
t_{rr}	$I_F = 7\text{ A}$, $-di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 100\text{ V}$, $V_{GS} = 0\text{ V}$	0.3	3	250 ns
Q_{RM}				μC
I_{RM}				A

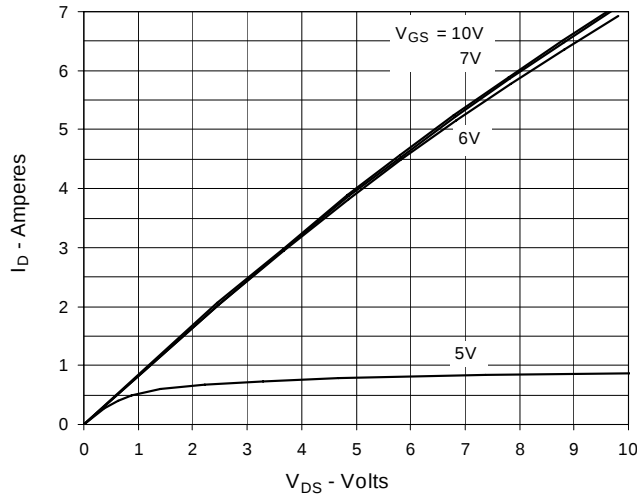
Notes: 1) Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

ISOLATED TO-220 (IXFP...M)


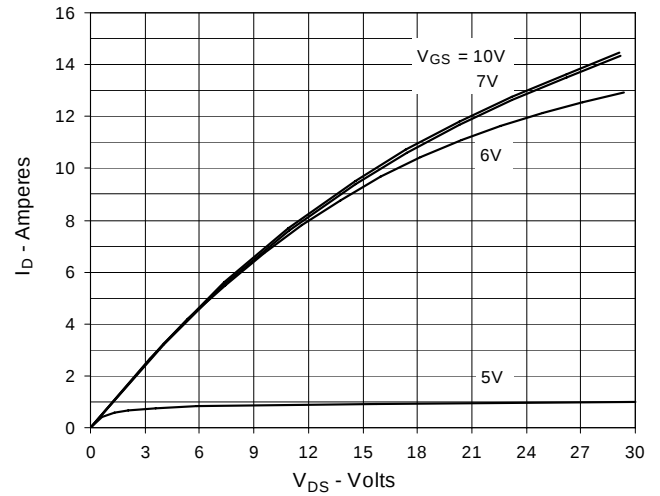
Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
$\varnothing P$	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

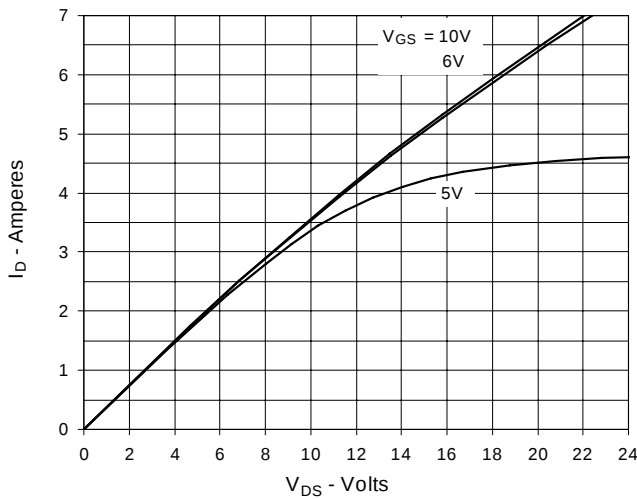
**Fig. 1. Output Characteristics
@ 25°C**



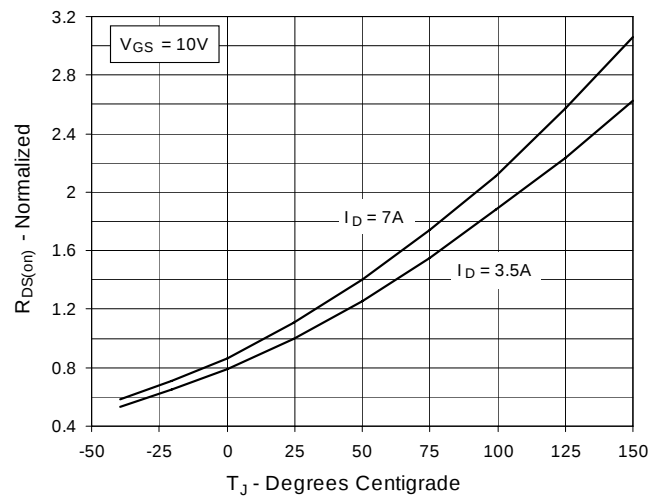
**Fig. 2. Extended Output Characteristics
@ 25°C**



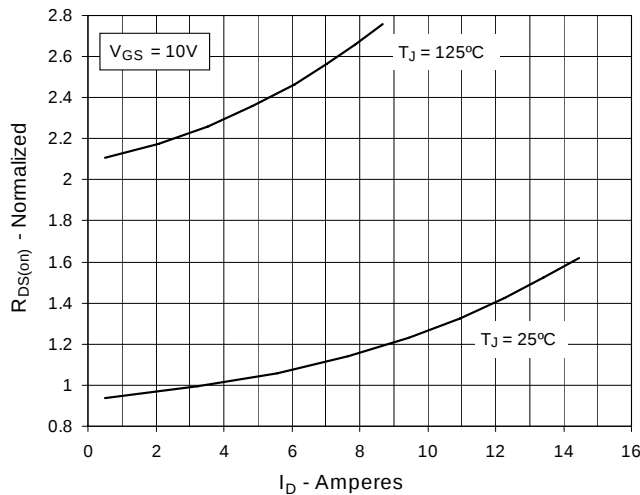
**Fig. 3. Output Characteristics
@ 125°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 3.5A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 3.5A$ Value
vs. Drain Current**



**Fig. 6. Maximum Drain Current vs.
Case Temperature**

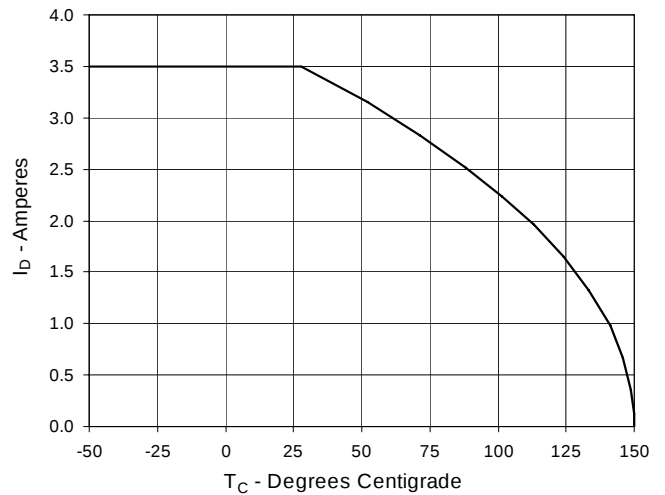


Fig. 7. Input Admittance

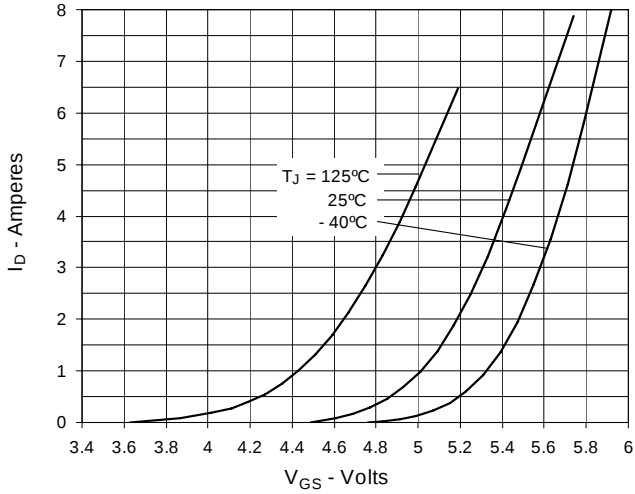


Fig. 8. Transconductance

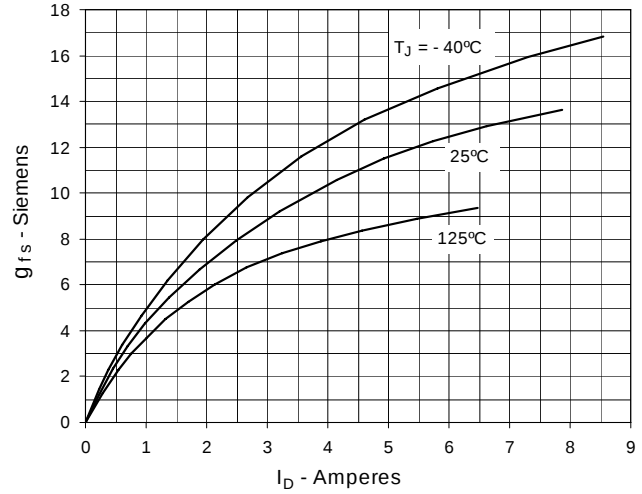


Fig. 9. Forward Voltage Drop of Intrinsic Diode

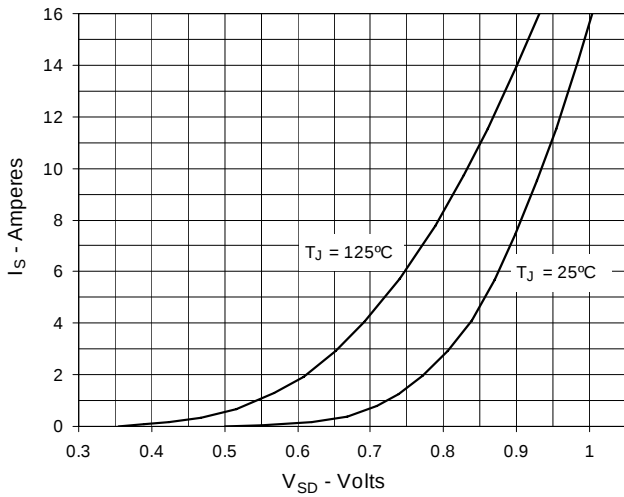


Fig. 10. Gate Charge

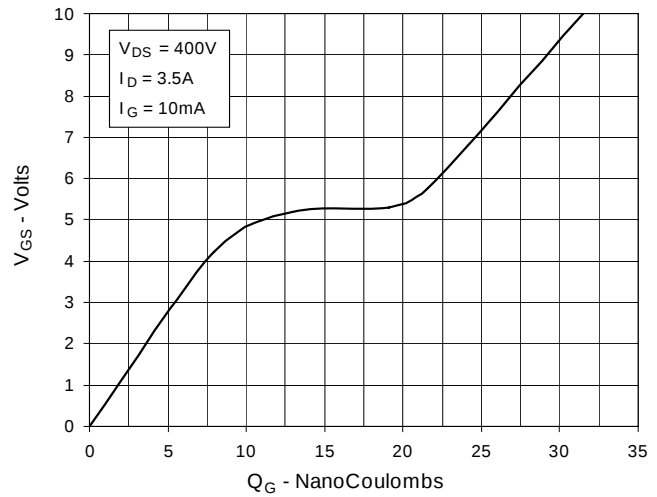


Fig. 11. Capacitance

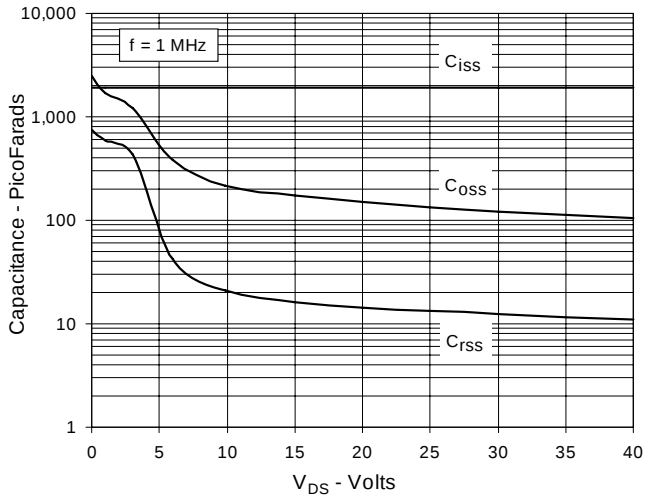


Fig. 12. Maximum Transient Thermal Resistance

